

wherein said some of the impurity regions are located between the plurality of channel regions in the semiconductor film,

D wherein a gate insulating film of a TFT in said driver circuit portion and a dielectric of a storage capacitor formed in said pixel portion comprise the same material and have the same film thickness, and

wherein the thickness of the gate insulating film of the TFT in said driver circuit portion is thinner than that of the gate insulating film of a TFT in the pixel portion.

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